



GaAs Schottky Diode

Technical Data

HSCH-9401

Features

- **Low Junction Capacitance**— typically 35 fF
- **Low Series Resistance**— typically 6 Ω
- **Tri-metal system for improved reliability**
- **High cut-off frequency**
- **Polyimide Passivation**
- **Durable Construction**

Description

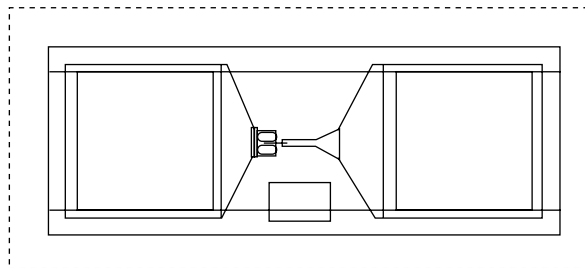
The HSCH-9401 is a discrete Schottky barrier diode fabricated with the Schottky Barrier Integrated Diode (SBID) process.

Applications

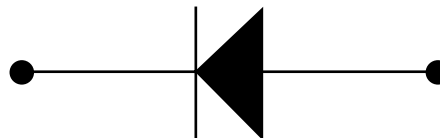
The HSCH-9401 is a general purpose millimeter wave diode that can be used as a detector or as a mixer in applications such as digital radio, LMDS, or video distribution.

Specifications

- **V_f (1 mA): 630-800 mV**
- **V_f (10 mA): 730-980 mV**
- **R_S (5 mA): <8.5 Ω**
- **B_V (-10 μ A): >6 V**
- **I_r (-2V): <200 nA**
- **C_j : <0.045 pF**



Chip Size:	610 x 255 μ m (24 x 10 mils)
Chip Size Tolerance:	± 10 μ m (± 0.4 mils)
Chip Thickness:	100 μ m (4 mils)
Chip Thickness Tolerance:	± 15 μ m (± 0.6 mils)
Bond Pad Sizes:	175 x 175 μ m (6.9 x 6.9 mils)





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This data sheet contains a variety of typical and guaranteed performance data. The information supplied should not be interpreted as a complete list of circuit specifications. In this data sheet the term *typical* refers to the 50th percentile performance. For additional information contact your local Agilent sales representative.

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Data subject to change.

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